

What is claimed is:

1. A method of manufacturing an active matrix display panel which comprises, for each pixel, a display element and a
5 thin film transistor for controlling connection between the display element and a power source line,

the method comprising the steps of:

forming the thin film transistor on a substrate; and

10 after formation of the thin film transistor, accumulating a plurality of layers to complete formation of the display element,

wherein

the step of accumulating a plurality of layers includes at least one step of forming a planarization insulating film
15 having a large thickness and an insulating property, and

the method further comprises, prior to the at least one step of forming a planarization insulating film, a step of disconnecting a line between the display element and the power source line with regard to a defective pixel.

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2. A method according to claim 1, wherein the line disconnection is performed by laser irradiation.

3. A method according to claim 1, wherein the display
25 element is an organic electroluminescence element.

4. A method of manufacturing an active matrix display panel which comprises, for each pixel, a display element and a thin film transistor for controlling connection between the display element and a power source line,

5 the method comprising the steps of:

forming the thin film transistor on a substrate;

forming a gate electrode of the thin film transistor and a line for the gate electrode;

10 forming source and drain electrodes of the thin film transistor and a line for connecting one of the source and drain electrodes to the power source line;

connecting the power source line to a power source, controlling application of a signal to the gate electrode of the thin film transistor, and performing a continuity test by
15 detecting the state of the electrode which is not connected to the power source line in accordance with an switching operation of the thin film transistor; and

with regard to a pixel which is determined by the continuity test to be defective, disconnecting a line between
20 the display element and the power source line via the thin film transistor,

wherein

the continuity test and the line disconnection is performed prior to completion of formation of the display
25 element.

5. A method according to claim 4, wherein the continuity test is performed after one electrode of the display element is formed.

5 6. A method according to claim 5, further comprising a step of forming an insulating film having high planarity after the continuity test and the line disconnection,

wherein a concave portion generated at the time of the line disconnection is repaired by the insulating film.

10 7. A method according to claim 4, wherein the line disconnection is performed by laser irradiation.

8. A method according to claim 4, wherein the display
15 element is an organic electroluminescence element.

9. An active matrix display panel which comprises, for each pixel, a display element and a thin film transistor for controlling connection between the display element and a power

20 source line,

the active matrix display panel comprising:

the thin film transistor formed on a substrate, one end of the thin film transistor being connected to the power source line;

25 an electrode of the display element connected to the other end of the thin film transistor; and

a planarization insulating film formed on the electrode,
wherein a line connecting the power source line and the
electrode is disconnected by laser irradiation, and a concave
portion formed by the laser irradiation is repaired by the
5 planarization insulating film.

10. A display panel according to claim 9, wherein
a further planarization insulating film different from the
planarization insulating film is formed covering the thin film
10 transistor, and the electrode is formed on the further
planarization insulating film.

11. A display panel according to claim 10, wherein the
display element is an organic EL element.

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